



(19)

(11) Publication number: **10317169 A**

Generated Document.

**PATENT ABSTRACTS OF JAPAN**(21) Application number: **10128453**(51) Intl. Cl.: **C23F 1/12 H01L 21/306**(22) Application date: **12.05.98**

(30) Priority:	<b>13.05.97 GB 97 9709659</b>	(71) Applicant: <b>SURFACE TECHNOL SYST LTD</b>
(43) Date of application publication:	<b>02.12.98</b>	(72) Inventor: <b>MCQUARRIE ANDREW DUNCAN BOMAN LEE CAMPBELL</b>
(84) Designated contracting states:		(74) Representative:

**(54) METHOD FOR ETCHING WORK AND APPARATUS THEREFOR**

(57) Abstract:

**PROBLEM TO BE SOLVED:** To improve the efficiency of an etching stage by continuously supplying gaseous XeF<sub>2</sub> and executing etching while the etching is heretofore executed by pulsatively supplying gaseous XeF<sub>2</sub>.

**SOLUTION:** An XeF<sub>2</sub> supplying section 12 consists of an XeF<sub>2</sub> source chamber 16 including a tray and ampoule 17 for an XeF<sub>2</sub> crystal 17a, a tank 18 via a valve 19, a flow rate controller 13 supplied with this material by the tank 18 and a valve 20 between the tank 18 and the flow rate controller 13. Pressure sources 21, 22 are provided respectively to maintain the tank 18 and the XeF<sub>2</sub> source chamber 16 at the sublimation pressure of the XeF<sub>2</sub>. This apparatus ensures the stable supply of the XeF<sub>2</sub> to an etching chamber.

COPYRIGHT: (C)1998,JPO

